

# Switch-mode Power Rectifiers

# MBR2535CTG, MBR2545CTG

The MBR2535CTG/45CTG series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

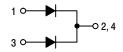
#### **Features**

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- These are Pb-Free Devices\*

#### **Mechanical Characteristics**

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

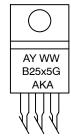
# SCHOTTKY BARRIER RECTIFIERS 30 AMPERES 35 and 45 VOLTS





TO-220 CASE 221A STYLE 6

#### **MARKING DIAGRAM**



1

A = Assembly Location Y = Year

WW = Work Week B25x5 = Device Code x = 3 or 4

G = Pb-Free Package AKA = Diode Polarity

### **ORDERING INFORMATION**

Device	Package	Shipping
MBR2535CTG	TO-220 (Pb-Free)	50 Units/Rail
MBR2545CTG	TO-220 (Pb-Free)	50 Units/Rail

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MBR2535CTG, MBR2545CTG

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR2535CTG MBR2545CTG	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	35 45	V
Average Rectified Forward Current (Rated $V_R$ , $T_C$ = 160°C)  Per Device  Per Diode	I <sub>F(AV)</sub>	30 15	А
Peak Repetitive Forward Current per Diode Leg (Rated $V_R$ , Square Wave, 20 kHz, $T_C$ = 150°C)	I <sub>FRM</sub>	30	Α
Non-Repetitive Peak Surge Current per Diode Leg (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I <sub>FSM</sub>	150	А
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I <sub>RRM</sub>	1.0	Α
Storage Temperature Range	T <sub>stg</sub>	-65 to +175	°C
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10,000	V/μs
ESD Ratings:  Machine Model = C  Human Body Model = 3B	ESD	> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 2)	R <sub>θJC</sub> R <sub>θJA</sub>	1.5 50	°C/W

<sup>2.</sup> When mounted using minimum recommended pad size on FR-4 board.

#### **ELECTRICAL CHARACTERISTICS** (Per Diode)

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Instantaneous Forward Voltage (Note 3)	I <sub>F</sub> = 15 A, T <sub>J</sub> = 25°C I <sub>F</sub> = 15 A, T <sub>J</sub> = 125°C I <sub>F</sub> = 30 A, T <sub>J</sub> = 25°C I <sub>F</sub> = 30 A, T <sub>J</sub> = 125°C	- - -	- 0.50 - 0.65	0.62 0.57 0.82 0.72	V
I <sub>R</sub>	Instantaneous Reverse Current (Note 3)	Rated dc Voltage, T <sub>J</sub> = 25°C Rated dc Voltage, T <sub>J</sub> = 125°C	-	- 9.0	0.2 25	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>1.</sup> The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

<sup>3.</sup> Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

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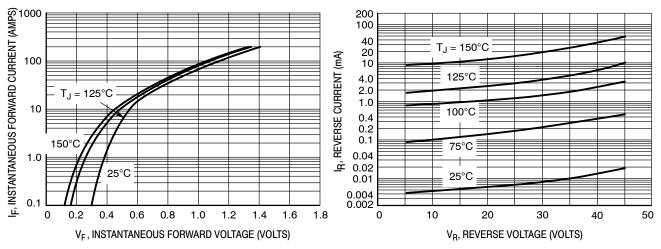


Figure 1. Typical Forward Voltage, Per Leg

Figure 2. Typical Reverse Current, Per Leg

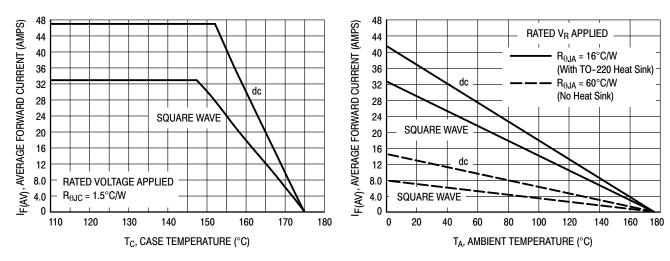


Figure 3. Current Derating, Per Device

Figure 4. Current Derating, Per Device

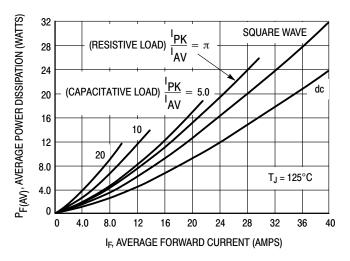


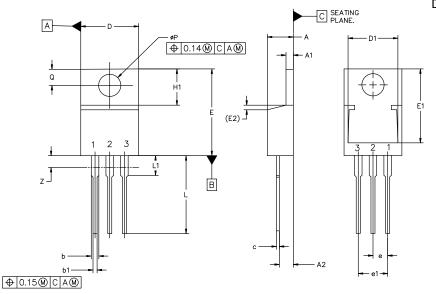
Figure 5. Forward Power Dissipation





#### TO-220-3 10.10x15.12x4.45, 2.54P CASE 221A **ISSUE AL**

**DATE 05 FEB 2025** 



NOM 4.45 1.28 2.42	MAX 4.83 1.41 2.79		
1.28	1.41		
2.42			
	2.79		
4 7 4			
1.54	1.52		
0.80	0.96		
0.49	0.61		
10.10	10.53		
8.63	8.83		
15.12	15.75		
12.78	12.98		
1.27 REF			
	0.49 10.10 8.63 15.12 12.78		

MILLIMETERS						
DIM	MIN	NOM	MAX			
е	2.42	2.54	2.66			
e1	4.83	5.08	5.33			
H1	5.97	6.22	6.47			
L	12.70	13.49	14.27			
L1	2.80	3.45	4.10			
Q	2.54	2.79	3.04			
ØΡ	3.60	3.85	4.09			
Z			3.48			

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:	:	STYLE 12:	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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